

Supplementary Materials: Two-Step Deposition of Silicon Films Using the Gas Phase Generation of Nanoparticles in the Chemical Vapor Deposition Process

Jae-Ho Suk, Sung-Chun Hong, Gil-Su Jang and Nong-Moon Hwang *

Department of Material Science and Engineering, College of Engineering at Seoul National University, 1 Gwanak-ro, Gwanak-gu, Seoul 08826, Korea; jhsuk@snu.ac.kr (J.-H.S.); brighthong@snu.ac.kr (S.-C.H.); gsjang@snu.ac.kr (G.-S.J.)

* Correspondence: nmhwang@snu.ac.kr

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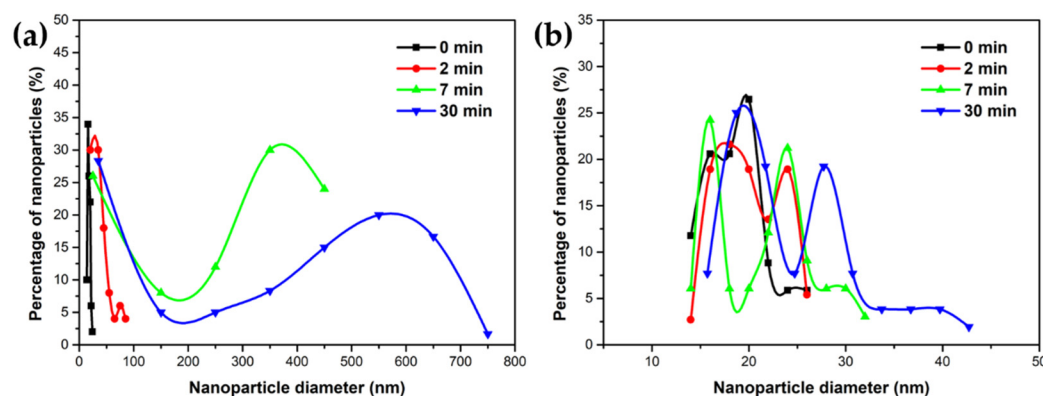


Figure S1. Size distributions of captured nanoparticles for delay times of 0, 2, 7 and 30 min (a) with and (b) without the nozzle tube.

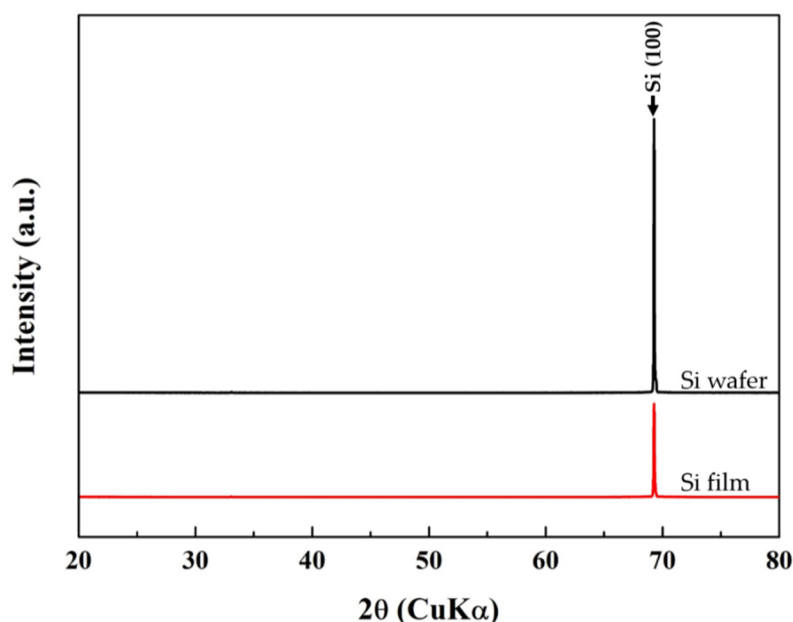


Figure S2. XRD data of the Si wafer and deposited Si film.

Table S1. EDS analysis of deposited Si thin film.

Element	Weight%	Atomic%
O	37.45	51.24
Si	62.55	48.76